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ABSTRACT

In a method for forming a stepped profile from a layer sequence (2) comprising a first patterning step, in which a first layer partial sequence (21) is removed apart from a first residual layer partial sequence (211), a second patterning step, in which a second layer partial sequence (22) located below the first layer partial sequence (21) is partially removed by means of etching with a second etchant, and a third patterning step, in which a third layer partial sequence (23) located below the second layer partial sequence (22) is partially removed by means of etching with a third etchant, according to the invention, a region of the second layer partial sequence (22) that is located below the first residual layer partial sequence (211) is removed in the second patterning step and the first projection (A) of the first residual layer partial sequence (211) is removed in the third patterning step.

(Figure 3)